

GAE

GREAT AMERICAN ELECTROINCS

BAL0102-150

Silicon NPN high power VHF transistor BAL0102-150 (transistor assembly) is designed for wideband push-pull power amplifiers required in AM or FM communication equipment (100-200 Mhz frequency range).

Output Power: 200 Watt
Frequency Range: 100-200 Mhz
Voltage: 28 V
Package Type: SOT-161 (8 Lead)
Common Emitter Configuration
Emitter Ballast Resistors
Internal Input Matching
Aluminum Metalization

Electrical Characteristics ($T_{CASE}=40^{\circ}C$)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
P_{out}	$f_o = 175 \text{ Mhz}/V_{cc}=28V/P_{IN}=36.4W$	200			W
G_p	$f_o = 175 \text{ Mhz}/V_{cc}=28V/P_{out}=200W$	7.5			dB
λ_c	$f_o = 175 \text{ Mhz}/V_{cc}=28V/P_{out}=200W$	60			%

ABSOLUTE MAXIMUM RATINGS ($T_{CASE} = 25^{\circ}C$)

SYMBOL	PARAMETERS	VALUE	UNIT
V_{CER}	Collector-Emitter Voltage, $R_{EB}=10\Omega$	50	V
V_{EBO}	Emitter-Base Voltage	4	V
I_c	Continuous Collector Current	18	A
P_C	Collector Power Dissipation	180*	W
T_j	Junction Temperature	160	$^{\circ}C$
$R_{th(j-c)}$	Junction-Case Thermal Resistance	0.6	$^{\circ}C/W$

*For Dynamic Operation, $T_{CASE} = 50^{\circ}C$

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